

# FMM7G50US60N

## Compact & Complex Module

### General Description

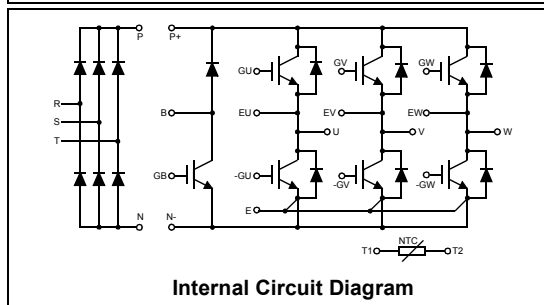
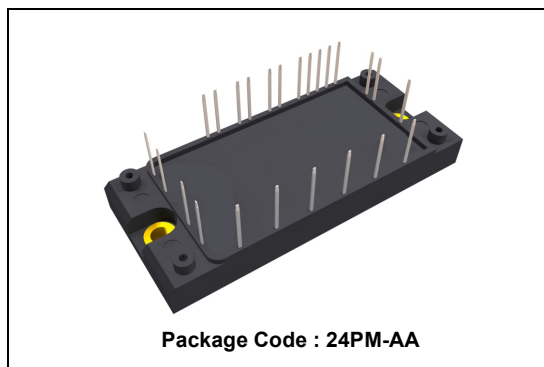
Fairchild IGBT Power Module provides low conduction and switching losses as well as short circuit ruggedness. It's designed for the applications such as motor control and general inverters where short-circuit ruggedness is required.

### Features

- Short Circuit rated Time 10us @  $T_C = 100^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$
- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 2.1\text{V}$  @  $I_C = 50\text{A}$
- High Input Impedance
- Built-in Brake & 3 Phase Rectifier Circuit
- Fast & Soft Anti-Parallel FWD
- Built-in NTC Thermistor
- UL Certified No. E209204

### Application

- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

	Symbol	Description	FMM7G50US60N	Units
Inverter & Brake	$V_{CES}$	Collector-Emitter Voltage	600	V
	$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
	$I_C$	Collector Current @ $T_C = 80^\circ\text{C}$	50	A
	$I_{CM(1)}$	Pulsed Collector Current	100	A
	$I_F$	Diode Continuous Forward Current @ $T_C = 80^\circ\text{C}$	50	A
	$I_{FM}$	Diode Maximum Forward Current	100	A
	$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	139	W
Converter	$T_{SC}$	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	us
	$V_{RRM}$	Repetitive Peak Reverse Voltage	1600	V
	$I_O$	Average Output Rectified Current	50	A
	$I_{FSM}$	Surge Forward Current @ 1Cycle at 60Hz, Peak value Non-Repetitive	320	A
Common	$i^2t$	Energy pulse @ 1Cycle at 60Hz	419	$\text{A}^2\text{s}$
	$T_J$	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
	$T_{STG}$	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
	$V_{ISO}$	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque		Mounting part Screw @ M4	4.0	N.m

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

**Electrical Characteristics of IGBT @ Inverter & Brake**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	Gate - Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA

**On Characteristics**

$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$I_C = 50mA, V_{CE} = V_{GE}$	5.0	6.5	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 50A, V_{GE} = 15V$	--	2.1	2.7	V

**Dynamic Characteristics**

$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	3565	--	pF
$C_{oes}$	Output Capacitance		--	286	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	60	--	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 50A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	90	200	ns
$t_r$	Rise Time		--	60	150	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	200	ns
$t_f$	Fall Time		--	120	250	ns
$E_{on}$	Turn-On Switching Loss		--	1.08	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.95	--	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 50A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	80	200	ns
$t_r$	Rise Time		--	60	150	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	200	ns
$t_f$	Fall Time		--	210	400	ns
$E_{on}$	Turn-On Switching Loss		--	1.28	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	1.5	--	mJ
$T_{sc}$	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V$ @ $T_C = 100^\circ C$	10	--	--	us
$Q_g$	Total Gate Charge	$V_{CE} = 300V, I_C = 50A,$ $V_{GE} = 15V$	--	150	300	nC
$Q_{ge}$	Gate-Emitter Charge		--	35	70	nC
$Q_{gc}$	Gate-Collector Charge		--	60	120	nC

**Electrical Characteristics of DIODE @ Inverter & Brake**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 50\text{A}$	$T_C = 25^\circ\text{C}$	--	1.9	2.8	V
			$T_C = 100^\circ\text{C}$	--	2.0	--	
$t_{rr}$	Diode Reverse Recovery Time		$T_C = 25^\circ\text{C}$	--	75	150	ns
			$T_C = 100^\circ\text{C}$	--	130	--	
$I_{rr}$	Diode Peak Reverse Recovery Current	$I_F = 50\text{A}$ $di / dt = 100 \text{ A/us}$	$T_C = 25^\circ\text{C}$	--	5	6.5	A
			$T_C = 100^\circ\text{C}$	--	7	--	
$Q_{rr}$	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	225	422	nC
			$T_C = 100^\circ\text{C}$	--	455	--	

**Electrical Characteristics of DIODE @ Converter**  $T_C = 25^\circ\text{C}$  unless otherwise noted

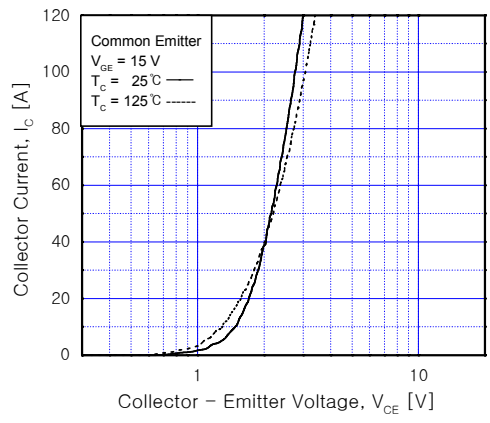
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units	
$V_{FM}$	Diode Forward Voltage	$I_F = 50\text{A}$	$T_C = 25^\circ\text{C}$	--	1.2	1.6	V
			$T_C = 100^\circ\text{C}$	--	1.2	--	
$I_{RRM}$	Repetitive Reverse Current	$V_R = V_{RRM}$	$T_C = 25^\circ\text{C}$	--	--	8	mA
			$T_C = 100^\circ\text{C}$	--	5	--	

**Thermal Characteristics**

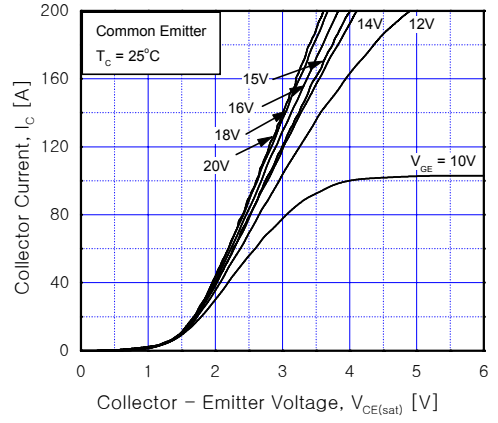
	Symbol	Parameter	Typ.	Max.	Units
Inverter	$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/6 Module)	--	0.9	$^\circ\text{C/W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	1.3	$^\circ\text{C/W}$
Brake	$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/6 Module)	--	0.9	$^\circ\text{C/W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	1.3	$^\circ\text{C/W}$
Converter	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	1.3	$^\circ\text{C/W}$
Weight		Weight of Module	210	--	g

**NTC Thermistor Characteristics**

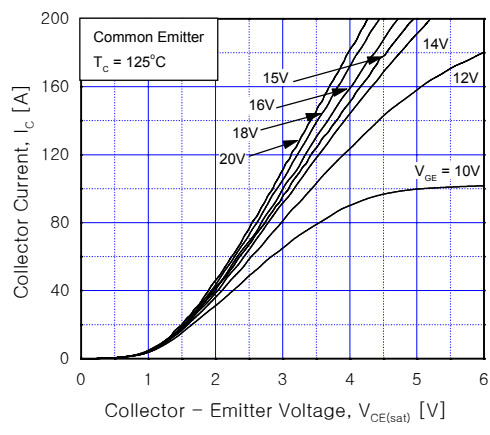
	Symbol	Parameter	Tol.	Typ.	Units
Thermistor	$R_{25}$	Rated Resistance @ $T_C = 25^\circ\text{C}$	+/- 5 %	5	$\text{K}\Omega$
	$R_{100}$	Rated Resistance @ $T_C = 100^\circ\text{C}$	+/- 5 %	0.415	$\text{K}\Omega$
	$B_{(25/100)}$	B - Value	+/- 3 %	3692	



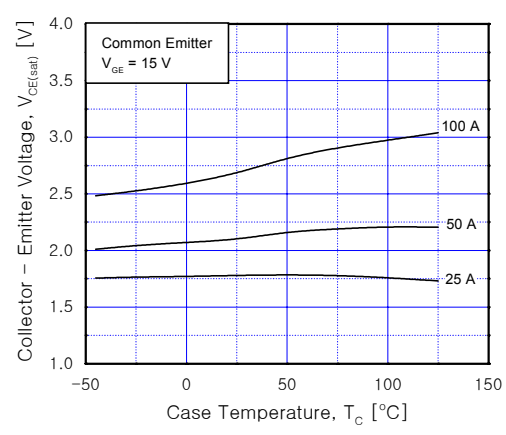
**Fig 1. Typical Output Characteristics**



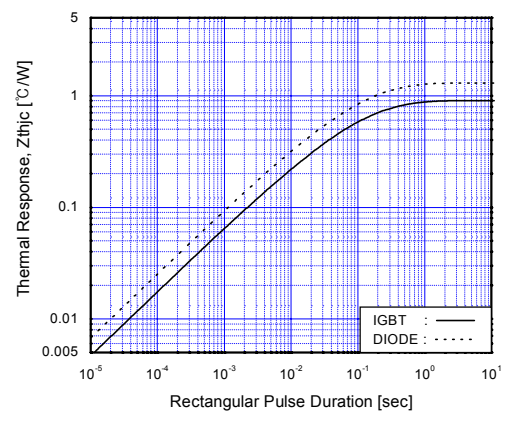
**Fig 2. Typical Saturation Voltage Characteristics**



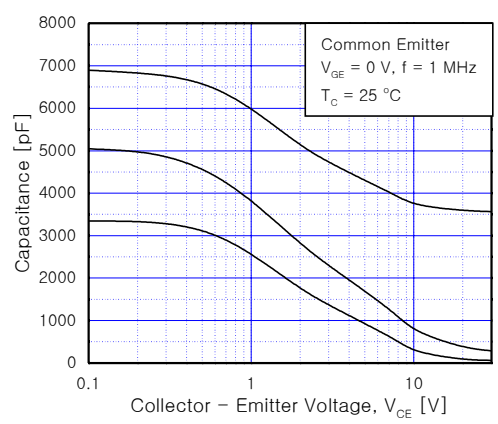
**Fig 3. Typical Saturation Voltage Characteristics**



**Fig 4. Saturation Voltage vs. Case Temperature at Variant Current Level**



**Fig 5. Transient Thermal Impedance**



**Fig 6. Capacitance Characteristics**

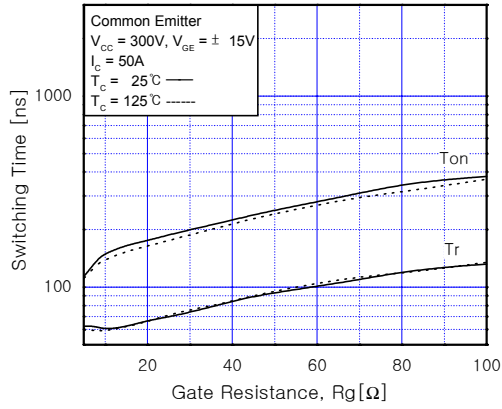


Fig 7. Turn-On Characteristics vs. Gate Resistance

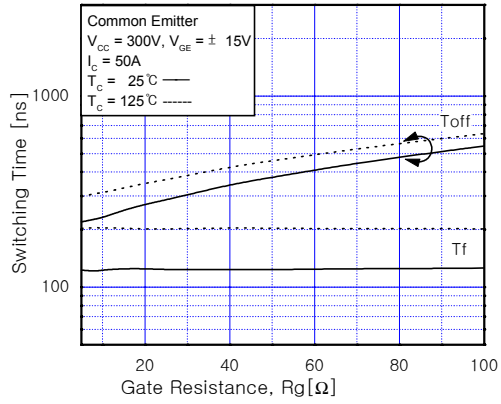


Fig 8. Turn-Off Characteristics vs. Gate Resistance

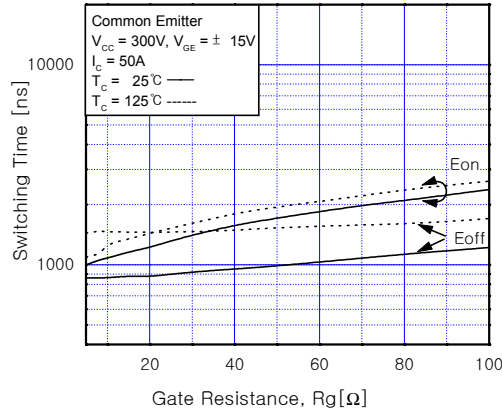


Fig 9. Switching Loss vs. Gate Resistance

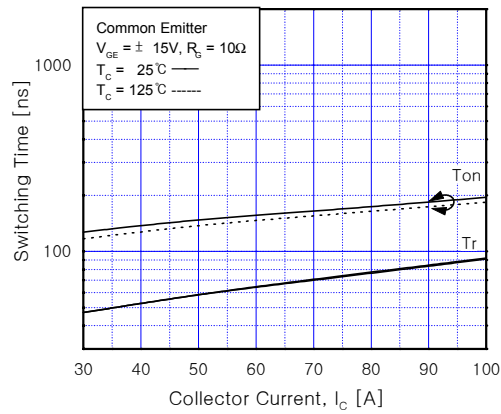


Fig 10. Turn-On Characteristics vs. Collector Current

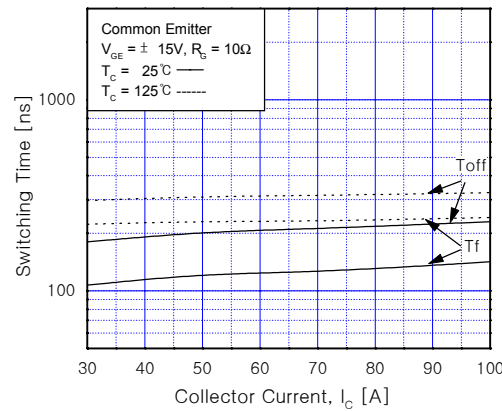


Fig 11. Turn-Off Characteristics vs. Collector Current

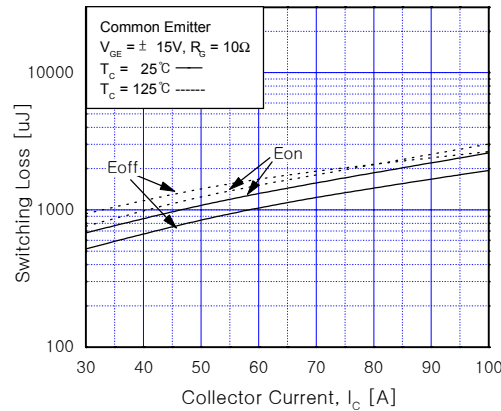


Fig 12. Switching Loss vs. Collector Current

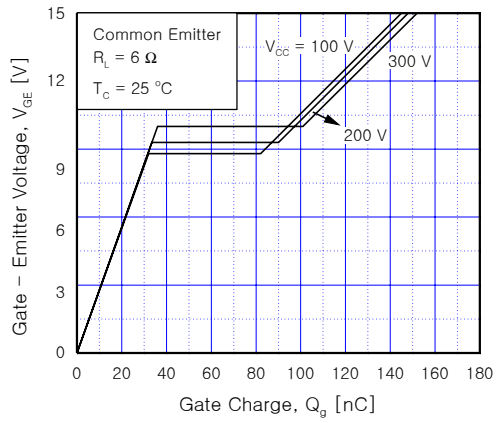


Fig 13. Gate Charge Characteristics

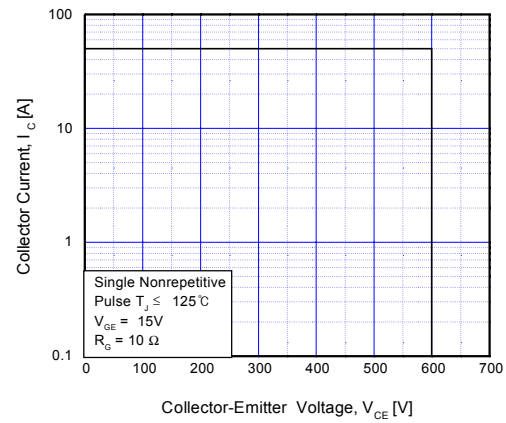


Fig 14. RBSOA Characteristics

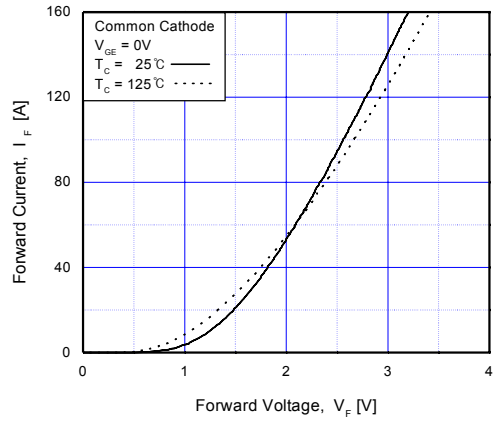


Fig 15. Forward Characteristics

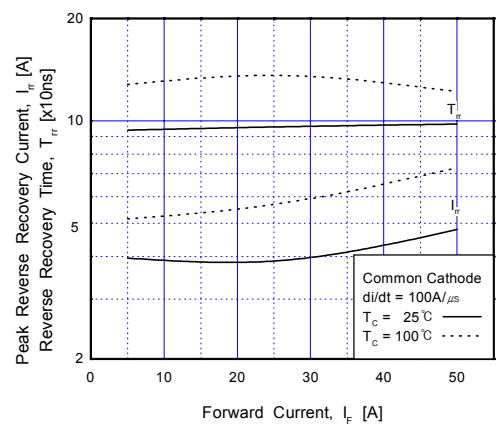


Fig 16. Reverse Recovery Characteristics

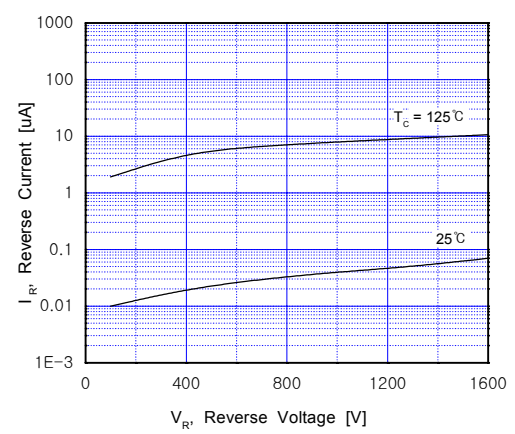


Fig 17. Rectifier ( Converter ) Characteristics

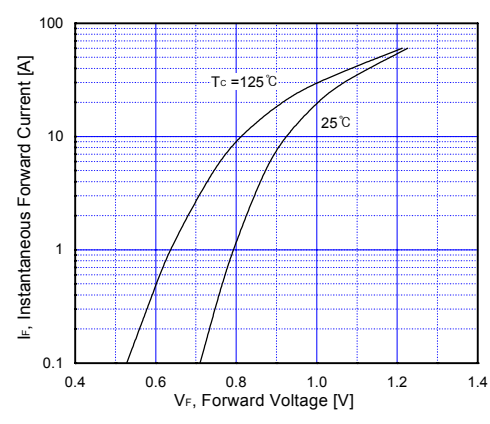


Fig 18. Rectifier ( Converter ) Characteristics

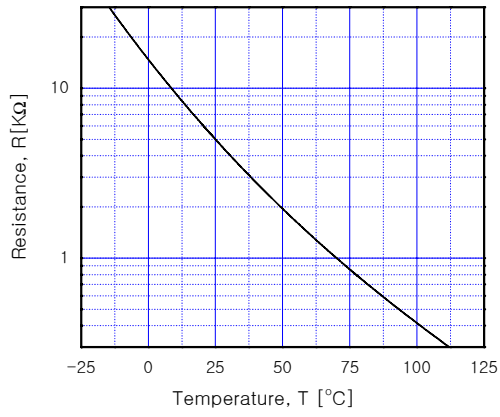


Fig 19. NTC Characteristics

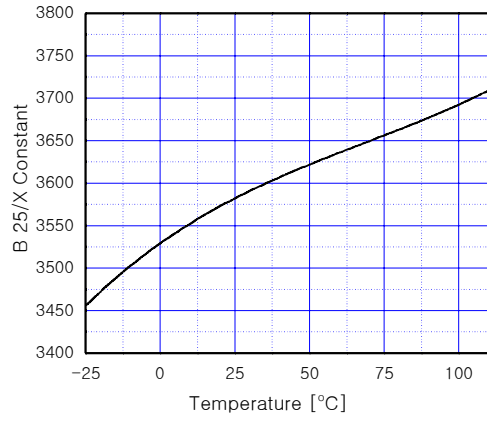
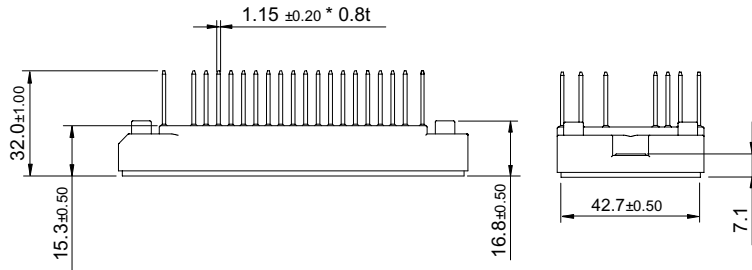
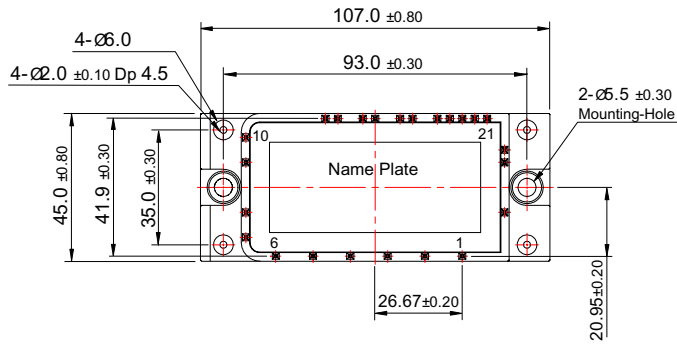


Fig 20. NTC Characteristics

Package Dimension

24PM-AA



-. Pin Coordinate

Pin #No	Coordinate	
	x	y
1	0.0	0.0
2	-11.43	0.0
3	-22.86	0.0
4	-34.29	0.0
5	-45.72	0.0
6	-57.15	0.0
7	-66.27	5.71
8	-66.27	13.33
9	-66.27	28.57
10	-66.27	36.19
11	-41.91	41.90
12	-38.10	41.90
13	-30.48	41.90
14	-26.67	41.90
15	-19.05	41.90
16	-15.24	41.90
17	-7.62	41.90
18	-3.81	41.90
19	0.0	41.90
20	3.81	41.90
21	7.62	41.90
22	12.93	32.38
23	12.93	28.57
24	12.93	13.33

- datum pin : #1
- Pin Tilt : ±0.20

Dimensions in Millimeters



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CROSSVOLT <sup>™</sup>	FRFET <sup>™</sup>	MicroPak <sup>™</sup>	QFET <sup>™</sup>	SuperSOT <sup>™</sup> -8
DOME <sup>™</sup>	GlobalOptoisolator <sup>™</sup>	MICROWIRE <sup>™</sup>	QS <sup>™</sup>	SyncFET <sup>™</sup>
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EnSigna <sup>™</sup>	I <sup>2</sup> C <sup>™</sup>	OCX <sup>™</sup>	RapidConfigure <sup>™</sup>	UHC <sup>™</sup>
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The Power Franchise <sup>™</sup>		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER <sup>®</sup>	VCX <sup>™</sup>
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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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